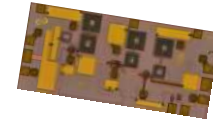




Let Performance Drive



CMD187

2-20 GHz Driver Amplifier

Features

- ▶ Wide bandwidth
- ▶ High linearity
- ▶ Low current consumption
- ▶ Small die size

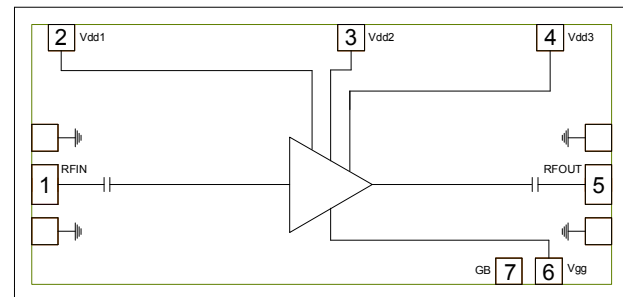
Description

The CMD187 is a wideband GaAs MMIC driver amplifier ideally suited for military, space and communications systems where small size and high linearity are needed. At 10 GHz the device delivers greater than 22 dB of gain with a corresponding output 1 dB compression point of +14 dBm and an output IP3 of 29 dBm. The CMD187 is a 50 ohm matched design which eliminates the need for external DC blocks and RF port matching. The CMD187 offers full passivation for increased reliability and moisture protection. This amplifier is the perfect alternative to higher cost hybrid amplifiers.

Applications

- ▶ Wideband communication systems
- ▶ Point-to-point radios
- ▶ Point-to-multi-point radios
- ▶ Military and space
- ▶ Test Instrumentation

Functional Block Diagram



Electrical Performance - $V_{dd} = 3.0\text{ V}$, $V_{gg} = 2.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, $F=10\text{ GHz}$

Parameter	Min	Typ	Max	Units
Frequency Range	2 - 20			GHz
Gain		22.5		dB
Input Return Loss		26		dB
Output Return Loss		23		dB
Output P1dB		14		dBm
Output IP3		29		dBm
Supply Current		115		mA

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Specifications

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, V _{dd}	5 V
Gate Voltage, V _{gg}	3 V
RF Input Power	+20 dBm
Channel Temperature, T _{ch}	150 °C
Power Dissipation, P _{diss}	655 mW
Thermal Resistance	99 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V _{dd}	3.0	3.0	5.0	V
I _{dd}		115		mA
V _{gg}		2.0		V

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

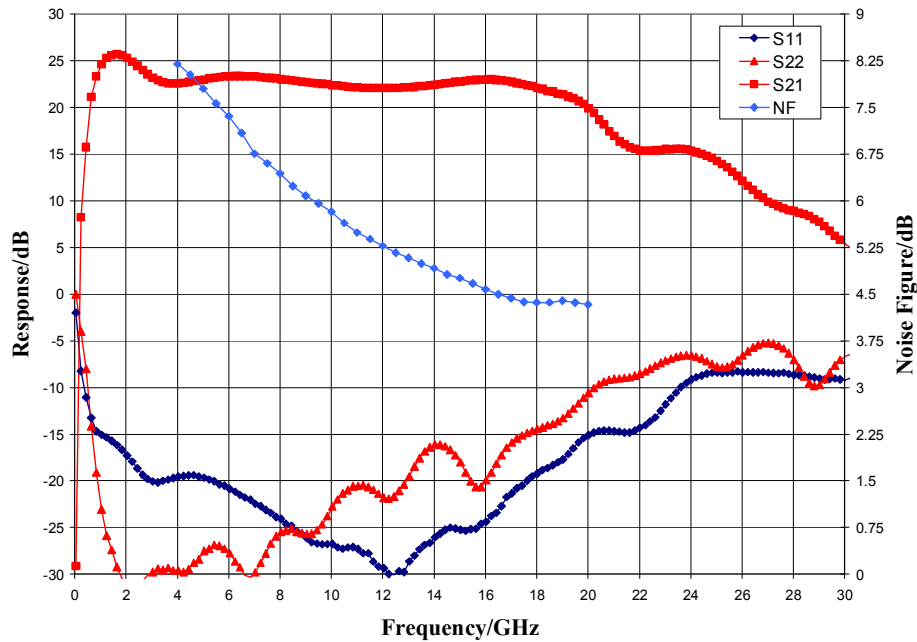
Electrical Specifications, V_{dd} = 3.0 V, V_{gg} = 2.0 V, T_A = 25 °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range	2 - 18		18 - 20				GHz
Gain	20	23	27	18	21.5	24	dB
Noise Figure		6			4.5		dB
Input Return Loss		25			17		dB
Output Return Loss		20			13		dB
Output P1dB	11	14		11	13.5		dBm
Output IP3		28			29		dBm
Supply Current	80	115	140	80	115	140	mA
Gain Temperature Coefficient		0.02			0.02		dB/°C
Noise Figure Temperature Coefficient		0.01			0.01		dB/°C

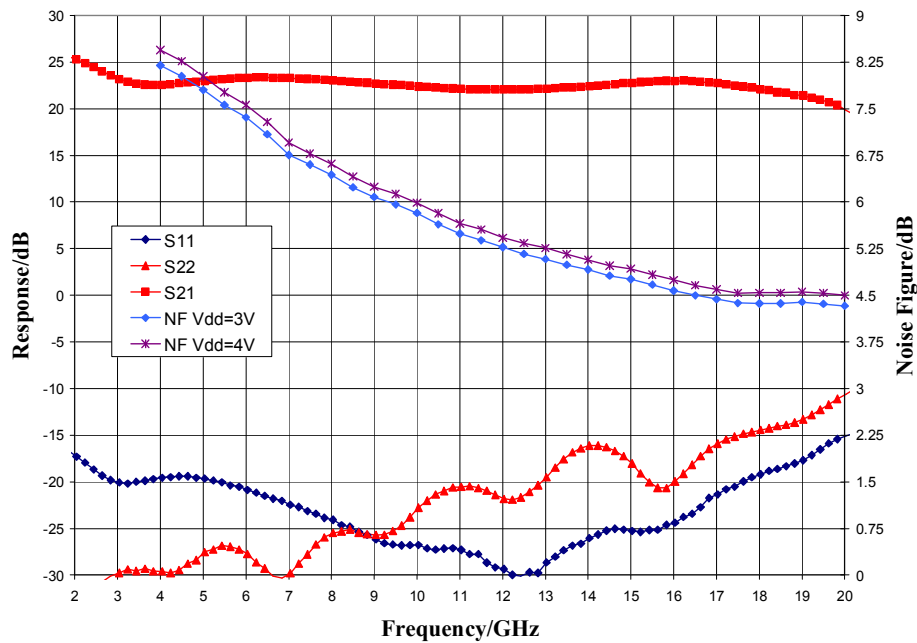
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Typical Performance

Broadband Performance, $V_{dd} = 3.0\text{ V}$, $V_{gg} = 2.0\text{ V}$, $I_{dd} = 115\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



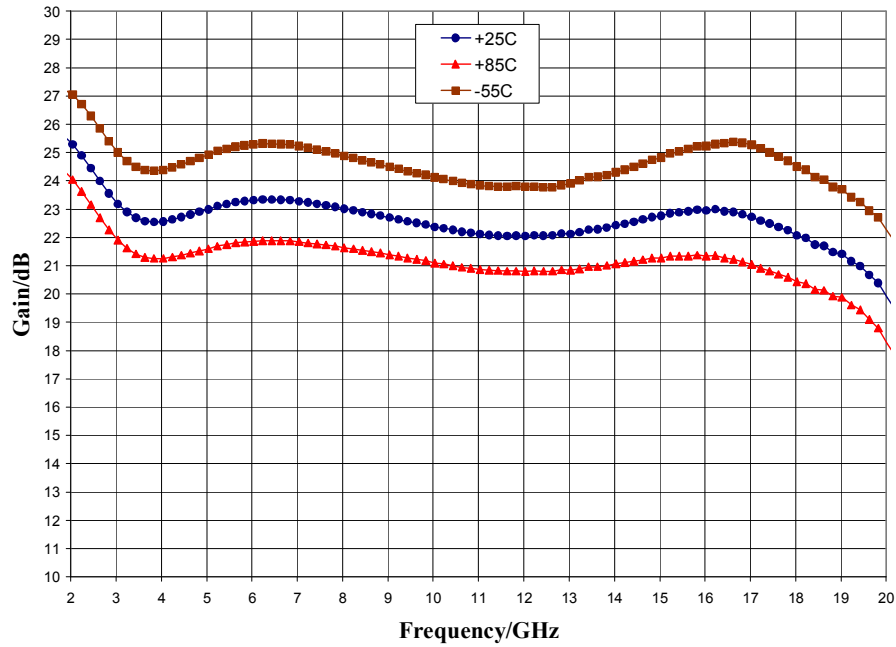
Narrow-band Performance, $V_{dd} = 3.0\text{ V}$, $V_{gg} = 2.0\text{ V}$, $I_{dd} = 115\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



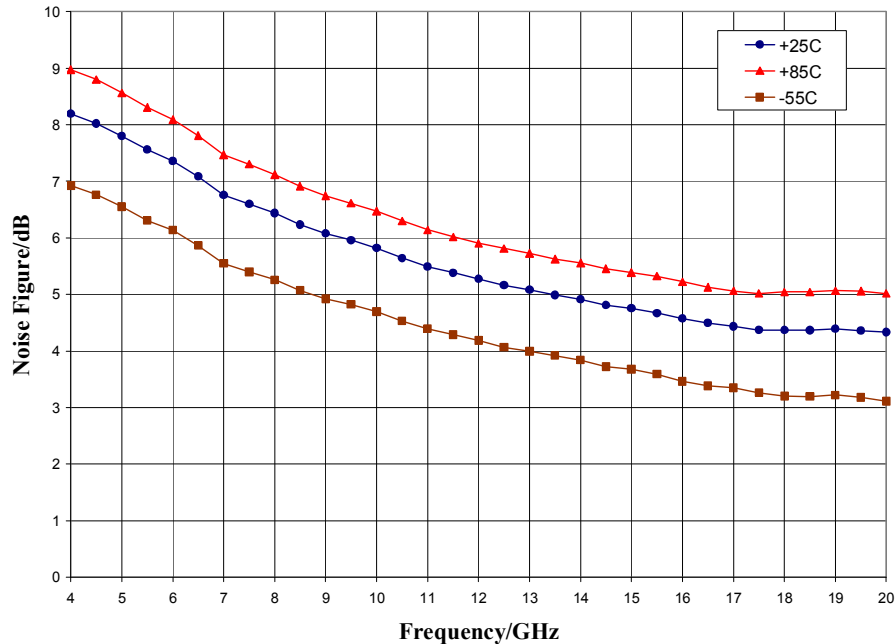
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Typical Performance

Gain vs. Temperature, $V_{dd} = 3.0\text{ V}$, $V_{gg} = 2.0\text{ V}$



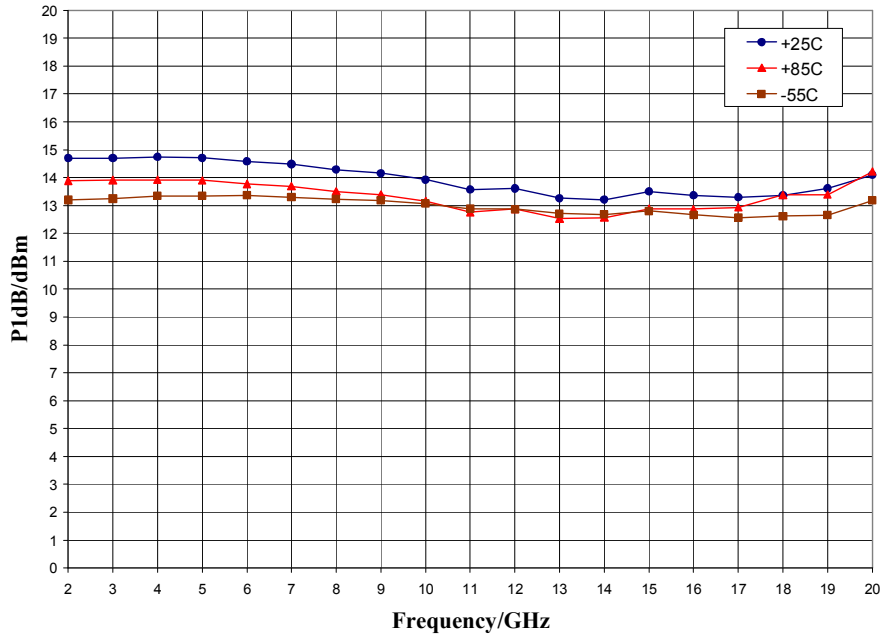
Noise Figure vs. Temperature, $V_{dd} = 3.0\text{ V}$, $V_{gg} = 2.0\text{ V}$



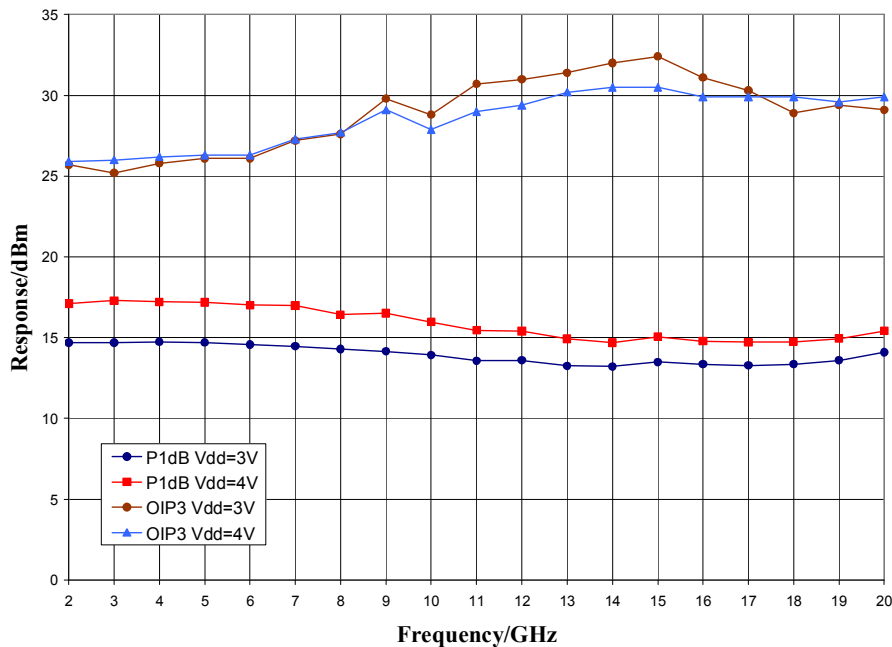
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Typical Performance

P1dB vs. Temperature, $V_{dd} = 3.0\text{ V}$, $V_{gg} = 2.0\text{ V}$



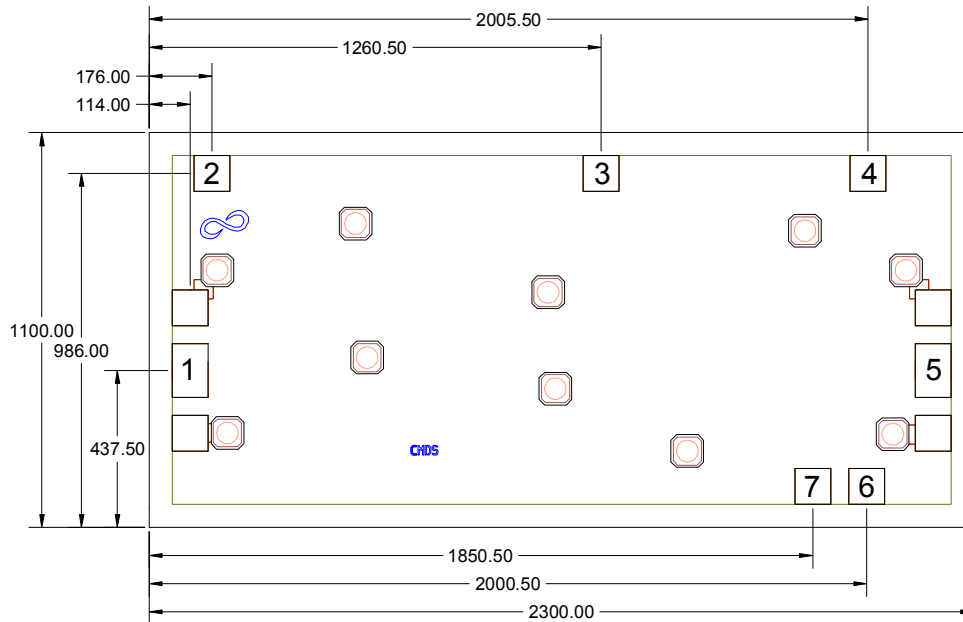
P1dB & Output IP3, $V_{dd}=3\text{V}$, 4V , $V_{gg} = 2.0\text{ V}$



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Mechanical Information

Die Outline (all dimensions in microns)

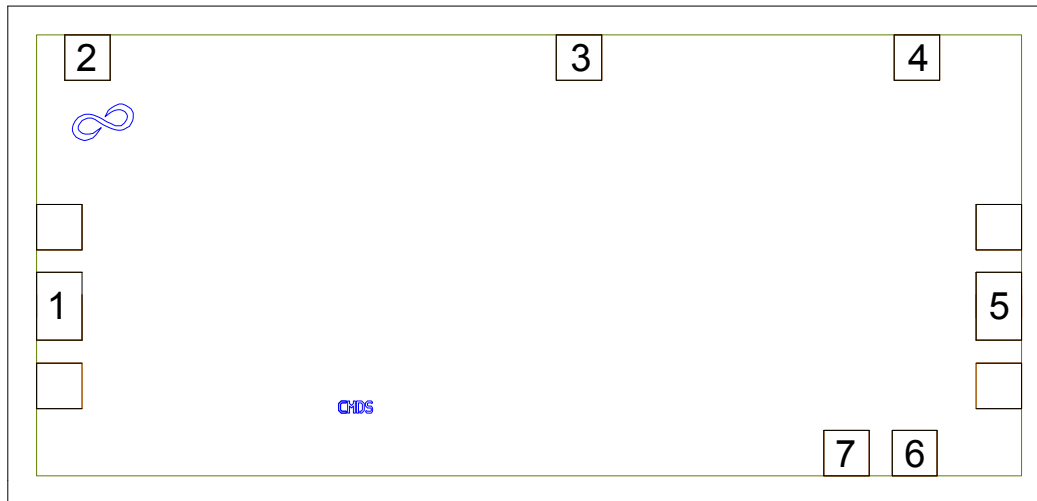


Notes:


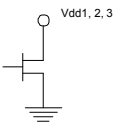

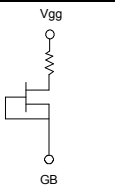

1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads are 100 microns square

Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC blocked and 50 ohm matched	
2, 3, 4	Vdd1, 2, 3	Power supply voltage Decoupling and bypass caps required	
5	RF out	DC blocked and 50 ohm matched	
6	Vgg	Power supply voltage Decoupling and bypass caps required	
7	GB	Connect to DC ground	
Backside	Ground	Connect to RF / DC ground	

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Applications Information

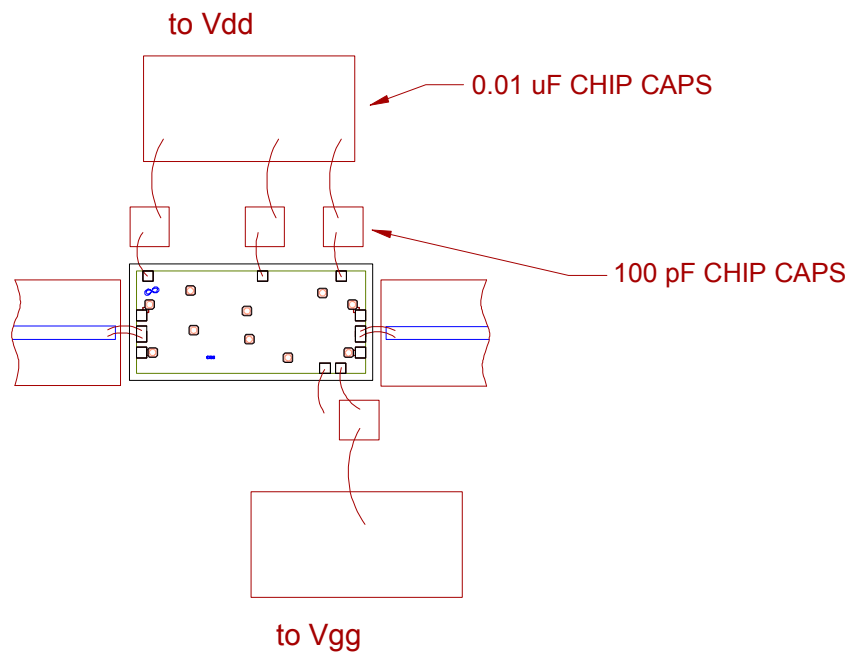
Assembly Guidelines

The backside of the CMD187 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85 μm thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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*Applications Information***Biasing and Operation**

The CMD187 is biased with a positive drain supply and positive gate supply. Performance is optimized when the drain voltage is set to +3.0 V. The recommended gate voltage is +2.0 V.

Turn ON procedure:

1. Apply drain voltage V_{dd} and set to +3 V
2. Apply gate voltage V_{gg} and set to +2 V

Turn OFF procedure:

1. Turn off gate voltage V_{gg}
2. Turn off drain voltage V_{dd}

RF power can be applied at any time.